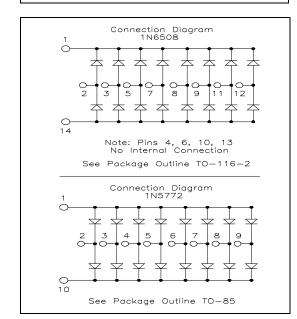


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1N5772 and 1N6508 JAN, JANTX, JANTXV

MIL -S-19500/474

PLANAR AIR-ISOLATED MONOLITHIC DIODE ARRAYS*



Features

- BV \geq 60 V @ 10 µA
- I_R ≤ 100 nA @ 40 V
- V_F ≤ 1.0 V @ 100 mA
- C...8.0 pF (MAX)

Absolute Maximum Ratings (Note 1)

Temperatures

- Storage Temperature Range: -65°C to +200°C
- Maximum Junction Operating Temperature: +150°C
- Lead Temperature: +260°C

Power Dissipation (Note 2)

- Maximum Dissipation per Junction at 25° C Ambient 400 mW
- Maximum Dissipation per Package at 25° C Ambient 1N5772 500 mW 1N6508 - 600 mW
- Linear Derating factor (from 25° C) Junction 3.2 mW / ° C
 Package 4.0 mW / ° C

Maximum Voltage and Currents

I_o Average Rectified Current Per Junction
 300 mA

I_{f (Surge)} Peak Forward Surge Current
 Pulse Width – 8.3 mS

Pulse Width = 8.3 mS 500 mA

Flectrical Characteristics (25°C Ambient Temperature unless otherwise noted)

CHARACTERISTIC	SYMBOL	MIN	MAX	UNITS	TEST CONDITIONS
Breakdown Voltage	BV	60		V	$I_R = 10 \mu\text{A}$
Forward Voltage	V _F		1.0	V	$V_F = 100 \text{ mA}$
-			1.5	V	$V_{F} = 500 \text{ mA}$
Reverse Current	I _R		100	nA	$V_R = 40 \text{ V}$
			50	μΑ	$V_R = 40 \text{ V}, T_A = 150^{\circ}\text{C}$
Capacitance (Note 3)	С		8.0	pF	$V_R = 0$, f = 1.0 MHz
Forward Recovery Time	t fr		40	ns	I _F = 500 mA
Reverse Recovery Time	t _{rr}			ns	
			20		$I_F = I_R = 200 \text{ mA}$
					$R_L = 100 \Omega i_{rr} = 20 \text{ mA}$

Notes!

- 1. The maximum ratings are limited values above which life satisfactory performance may be impaired.
- 2. These are steady state limits. The factory should be consulted or applications involving pulsed or low duty cycle operations.
- The capacitance is measured from pin to pin across any one of the diodes. The interaction of other diodes is therefore included in the measured value.
- * 16 DIODE CORE DRIVER MATRIX

